

## **SOT-23 Plastic-Encapsulate Transistors**

**S8050** TRANSISTOR (NPN)

FEATURES Complimentary to S8550 Collector current:lc=0.5A

MARKING:J3Y

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol (符号)	Parameter (参数名称)	Value (额定值)	Units (单位)		
VCBO	Collector-Base Voltage (集电极-基极电压)	40 V			
VCEO	Collector-Emitter Voltage (集电极-发射极电压)	25	V		
VEBO	Emitter-Base Voltage (发射极-基极电压)	5	V		
IC	Collector Current -Continuous (集电极电流)	0.5	А		
PC	Collector Power Dissipation (耗散功率)	0.3	W		
Tj	Junction Temperature (结温)	150 ℃			
Tstg	Storage Temperature (储存温度)	-55-150	$^{\circ}$ C		

## **ELECTRICAL CHARACTERISTICS** (Tamb=25°C unless otherwise specified)

Parameter (参数名称)	Symbol (符号)	Test conditions (测试条件)	MIN (最小值)	TYP (典型值)	MAX (最大值)	UNIT (单位)
Collector-base breakdown voltage 集电极-基极击穿电压	V(BR)CBO	IC= 100μA, IE=0	40			V
Collector-emitter breakdown voltage 集电极-发射极击穿电压	V(BR)CEO	IC= 1mA, IB=0	25			V
Emitter-base breakdown voltage 发射极-基极击穿电压	V(BR)EBO	IE=100μA, IC=0	5			V
Collector cut-off current 集电极-基极截止电流	ICBO	VCB=30 V , IE=0			1	μА
Collector cut-off current 集电极-发射极截止电流	ICEO	VCE=25V , IB=0			10	μА
Emitter cut-off current 发射极-基极截止电流	IEBO	VEB=5V , IC=0			1	μА
DC current gain 直流电流增益	hFE	VCE=1V, IC= 50mA	80		400	
Collector-emitter saturation voltage 集电极-发射极饱和压降	VCE(sat)	IC=500mA, IB= 50mA			0.5	V
Base-emitter saturation voltage 发射极-基极饱和压降	VBE(sat)	IC=500mA, IB= 50mA			1.2	V

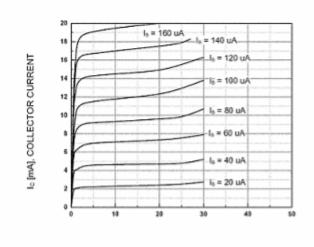
## **CLASSIFICATION OF hFE**

<b>Range</b> 100-200	200-400	300-400	400-600
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## **Typical Characteristics**



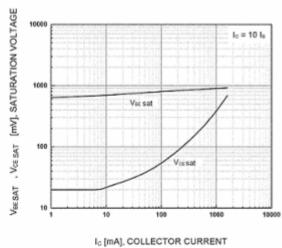
1000 TOOO TOOO TOOO TOOO

VOE [V], COLLECTOR-EMITTER VOLTAGE

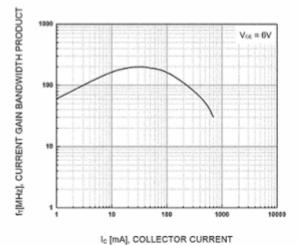
Static Characteristic

 $I_{\text{C}}$  [mA], COLLECTOR CURRENT

DC current Gain



e



Current Gain Bandwidth Product

Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

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